

Product data sheet

1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1608D-2 (SOD1608) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

2. Features and benefits

- Average forward current: $I_{F(AV)} \le 2 A$
- Reverse voltage: V_R ≤ 20 V
- Low forward voltage $V_F \le 450 \text{ mV}$
- Low reverse current
- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

4. Quick reference data

| Table 1. Qui | ck reference data | | | | | | |
|--------------------|----------------------------|---|-----|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
| I _{F(AV)} | average forward current | δ < 0.5; f = 20 kHz; T _{sp} ≤ 130 °C; square wave | | - | - | 2 | A |
| | | δ < 0.5; f = 20 kHz; T _{amb} ≤ 65 °C; square wave | [1] | - | - | 2 | A |
| V _R | reverse voltage | T _j = 25 °C | | - | - | 20 | V |
| V _F | forward voltage | I_{F} = 2 A; pulsed; t_{p} \leq 300 $\mu s;$ δ \leq 0.02; T_{j} = 25 $^{\circ}C$ | | - | 395 | 450 | mV |





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| Symbol | Parameter | Conditions | | Min | Тур | Мах | Unit |
|-------------------------|-----------------------|---|--|-----|-----|-----|------|
| I _R | reverse current | V _R = 10 V; T _j = 25 °C | | - | 70 | 350 | μA |
| Dynamic characteristics | | | | | | | |
| t _{rr} | reverse recovery time | $I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 ^{\circ}\text{C}$ | | - | 5 | - | ns |

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

5. Pinning information

| Table 2. | Pinning | information | | |
|----------|---------|-------------|---|----------------|
| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| 1 | к | cathode[1] | | 1 🛃 2 |
| 2 | A | anode | | sym001 |
| | | | Transparent top view DFN1608D-2 (SOD1608) | |

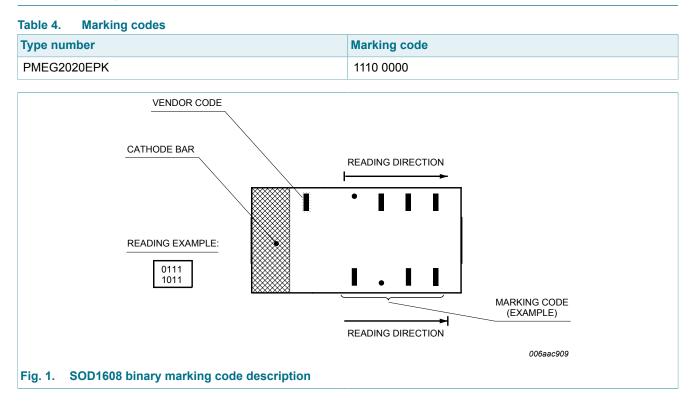
[1] The marking bar indicates the cathode.

6. Ordering information

| Table 3. Ordering information | | | | | | |
|---------------------------------------|------------|---|---------|--|--|--|
| Type number | Package | | | | | |
| | Name | Description | Version | | | |
| PMEG2020EPK | DFN1608D-2 | DFN1608D-2: leadless ultra small plastic package; 2 terminals | SOD1608 | | | |

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7. Marking



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Мах | Unit |
|--------------------|-------------------------------------|---|-----|-----|------|------|
| V _R | reverse voltage | T _j = 25 °C | | - | 20 | V |
| I _F | forward current | T _{sp} ≤ 125 °C | | - | 2.83 | А |
| I _{F(AV)} | average forward current | δ < 0.5; f = 20 kHz; T _{sp} ≤ 130 °C; square wave | | - | 2 | A |
| | | δ < 0.5; f = 20 kHz; T _{amb} ≤ 65 °C; square wave | [1] | - | 2 | A |
| I _{FRM} | repetitive peak forward current | t _p = 1 ms; δ = 0.25 | | - | 4 | А |
| I _{FSM} | non-repetitive peak forward current | t_p = 8 ms; $T_{j(init)}$ = 25 °C; square wave | | - | 5 | А |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [2] | - | 415 | mW |
| | | | [3] | - | 895 | mW |
| | | | [1] | - | 1565 | mW |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

9. Thermal characteristics

| Thermal characteristics | | | | | | | |
|--|--|-------------|--------|-----|-----|-----|------|
| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
| R _{th(j-a)} thermal resistance from junction to ambient | thermal resistance | in free air | [1][2] | - | - | 300 | K/W |
| | - | | [1][3] | - | - | 140 | K/W |
| | ambient | | [1][4] | - | - | 80 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | [5] | - | - | 20 | K/W |

 For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

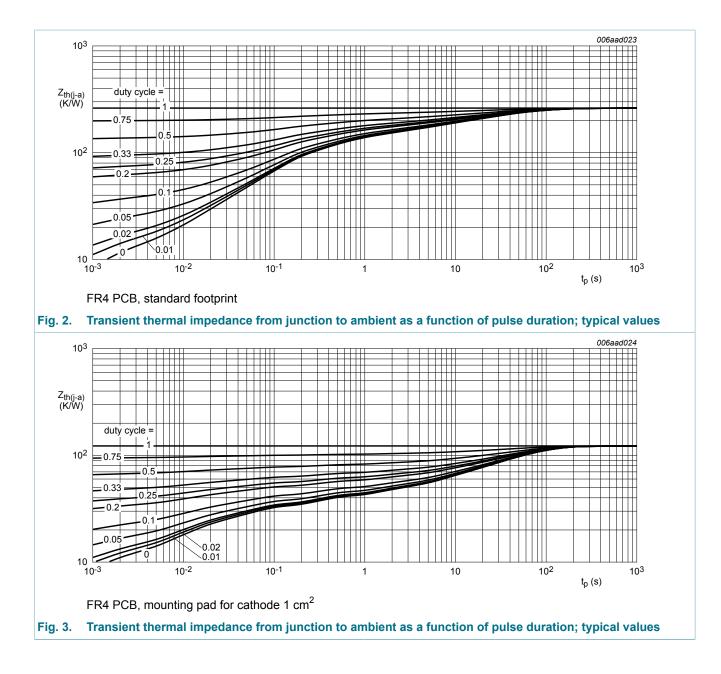
^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[5] Soldering point of cathode tab.

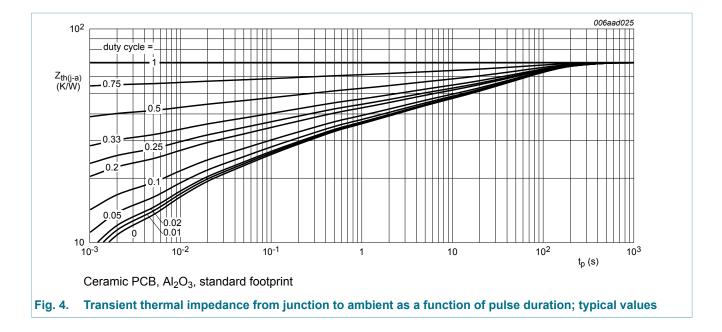
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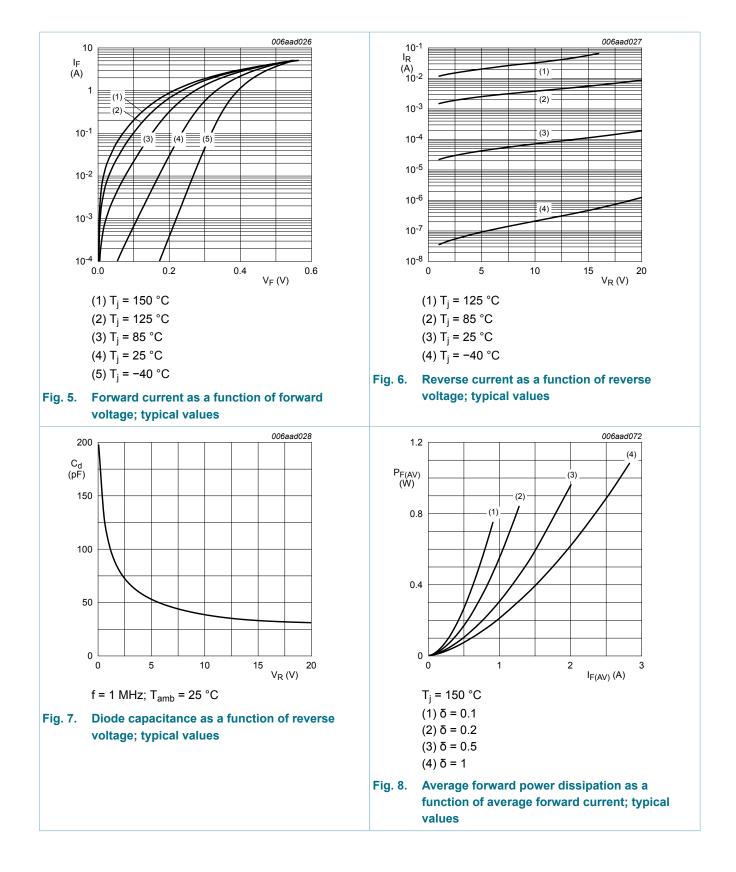


10. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Мах | Unit |
|----------------------------------|---|---|-----|-----|-----|------|
| V _F forward voltage | forward voltage | I_F = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 230 | 260 | mV |
| | I _F = 500 mA; pulsed; t _p ≤ 300 μs; $\delta \le 0.02$; T _j = 25 °C | - | 290 | 330 | mV | |
| | I _F = 1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 330 | 380 | mV | |
| | | I _F = 2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _j = 25 °C | - | 395 | 450 | mV |
| R reverse current | V _R = 10 V; T _j = 25 °C | - | 70 | 350 | μA | |
| | | V _R = 20 V; T _j = 25 °C | - | 220 | 900 | μA |
| C _d diode capacitance | diode capacitance | V _R = 1 V; f = 1 MHz; T _j = 25 °C | - | 105 | 120 | pF |
| | | V _R = 10 V; f = 1 MHz; T _j = 25 °C | - | 40 | 50 | pF |
| Dynamic cl | naracteristics | | | | | |
| t _{rr} | reverse recovery time | $I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$ | - | 5 | - | ns |
| V _{FRM} | peak forward recovery voltage | $I_F = 0.5 \text{ A}; \text{ d}I_F/\text{d}t = 20 \text{ A}/\mu\text{s}; T_j = 25 \text{ °C}$ | - | 320 | - | mV |

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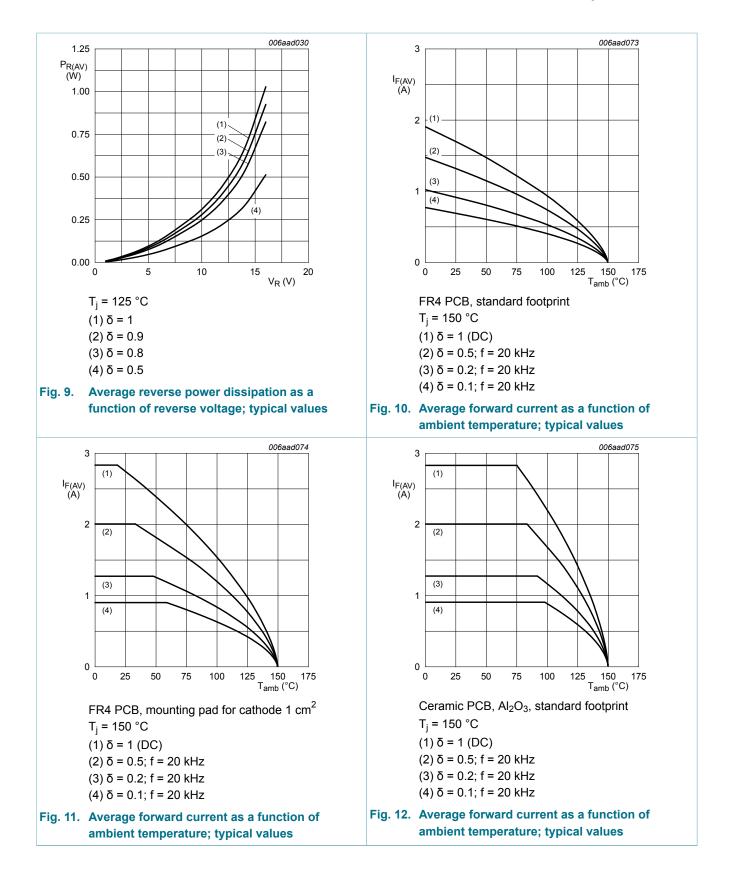
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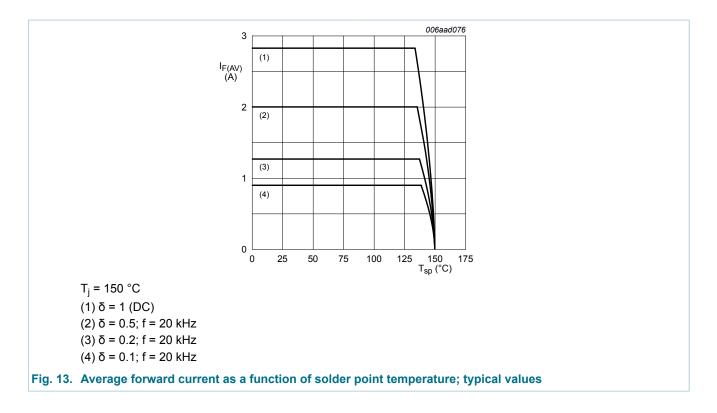
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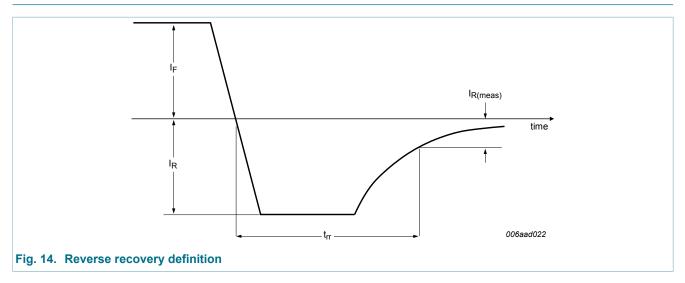


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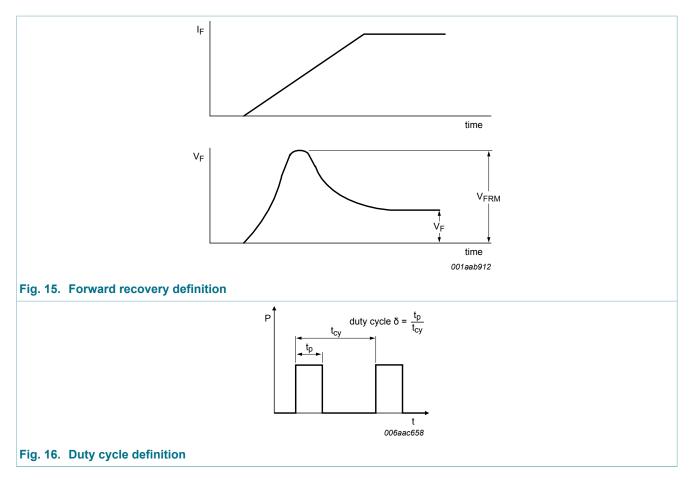


11. Test information



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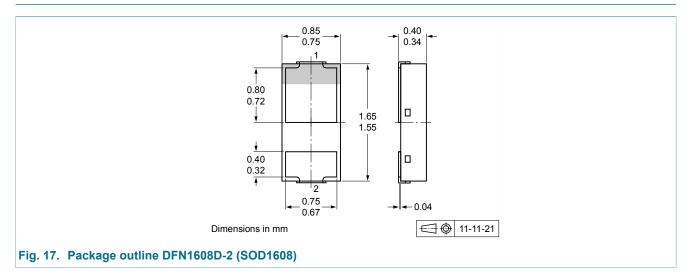
The current ratings for the typical waveforms are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current, $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering

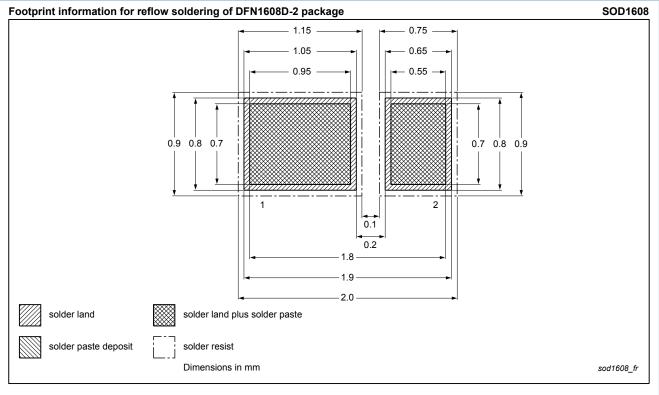


Fig. 18. Reflow soldering footprint for DFN1608D-2 (SOD1608)

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14. Revision history

| Table 8. Revision hi | story | | | |
|----------------------|------------------------|--------------------|---------------|-----------------|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
| PMEG2020EPK v.2 | 20140210 | Product data sheet | - | PMEG2020EPK v.1 |
| Modifications: | Marking code corrected | • | | |
| PMEG2020EPK v.1 | 20120425 | Product data sheet | - | - |

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15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [<u>3]</u> | Definition |
|--------------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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